

Super-Junction Power Mosfet

1. Product Information

Features

- Low FOM $R_{DS(ON)} \times Q_G$
- Fast switching capability
- Lead free product is acquired

Applications

- Power supply
- Charger
- Solar/UPS-Micro inverter system

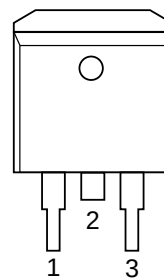
Quick reference

- $V_{DS} \geq 650\text{ V}$
- $I_D \leq 25\text{ A}$
- $R_{DS(ON)} \leq 140\text{ m}\Omega @ V_{GS} = 10\text{ V}$ (Type 110 m Ω)

Pin Description

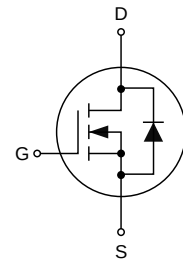
Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Simplified Outline



TO-263
Top View

Symbol



Package Marking and Ordering Information

Part number	Marking	Package	Packaging	Quantity	Reel size	Tape width
KJCF65R140D	KJCF65R140D	TO-263	☒ Tape & Reel	800 PCS	13"	24 mm
			☐ Tube	N/A	N/A	N/A

2. Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Continuous Drain Current (T _C =25°C)	25	A
	Continuous Drain Current (T _C =100°C)	19.4	A
I_{DM}	Pulsed Drain Current	75	A
E_{AS}	Single Pulsed Avalanche Energy (L=30 mH)	120	mJ
dv/dt	Peak Diode Recovery dv/dt	50	V/ns
I_S	Continuous diode forward current	25	A
P_D	Power Dissipation	198	W
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
R _{θJA}	Thermal Resistance, Junction-Ambient	72	°C/W
R _{θJC}	Thermal Resistance, Junction-Case	0.63	°C/W

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250 μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650 V, V _{GS} =0 V	-	-	5	μA
		V _{DS} =650 V, T _C =150°C	-	225	-	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±30 V, V _{DS} =0 V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250 μA	3.0	-	4.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10 V, I _D =12 A	-	110	140	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =100 V, V _{GS} =0 V, f=1 MHz	-	1600	-	pF
C _{oss}	Output Capacitance		-	93	-	pF
C _{rss}	Reverse Transfer Capacitance		-	1.8	-	pF
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =400 V, I _D =12 A, R _G =27 Ω, V _{GS} =10 V	-	63	-	ns
t _r	Turn-on Rise Time		-	60	-	ns
t _{d(off)}	Turn-off Delay Time		-	148	-	ns
t _f	Turn-off Fall Time		-	32	-	ns
R _{g,int}	Gate resistance	f=1 MHz	-	10	-	Ω
Q _g	Total Gate Charge	V _{DS} =520 V, I _D =12 A, V _{GS} =10 V	-	45	-	nC
Q _{gs}	Gate-Source Charge		-	13	-	nC
Q _{gd}	Gate-Drain Charge		-	23	-	nC
Source-Drain Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0 V, I _F =12 A	-	0.85	1.15	V
Q _{rr}	Reverse Recovery Time	V _R =400 V, I _F =12 A, di/dt=100 A/μs	-	0.65	-	μC
T _{rr}	Reverse Recovery Charge		-	182	-	ns

4. Electrical Characteristics

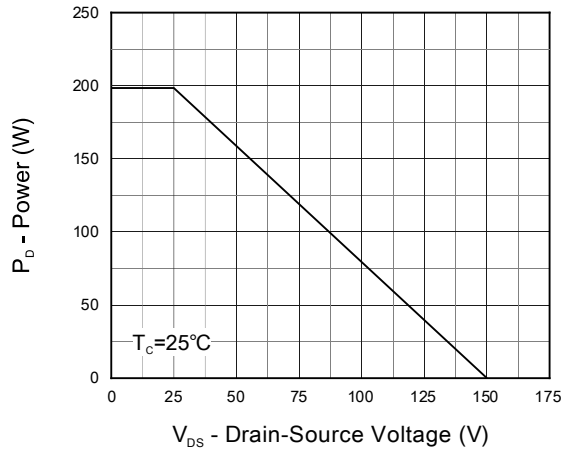


Fig 1. Power Capability

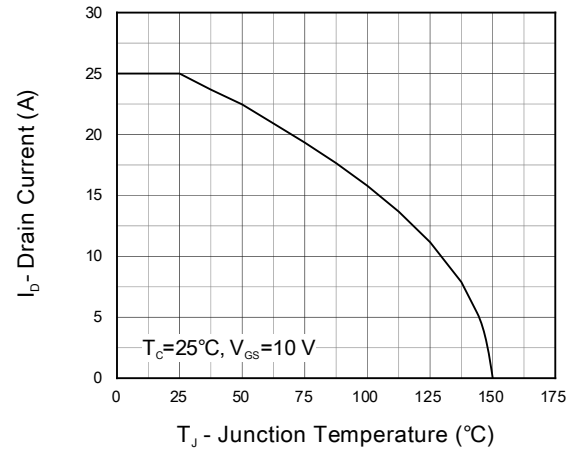


Fig 2. Current Capability

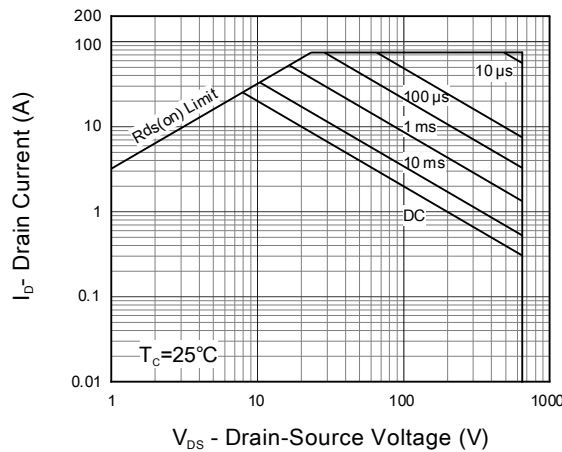


Fig 3. Safe Operation Area

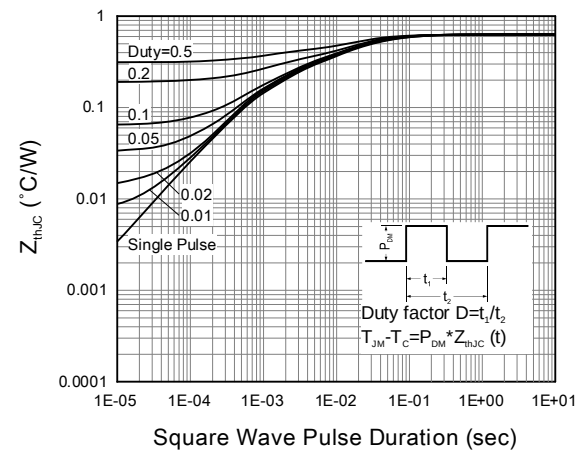


Fig 4. Transient Thermal Impedance

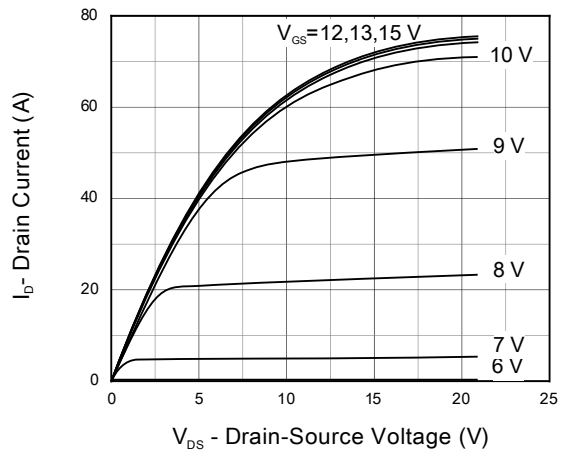


Fig 5. Output Characteristics
 $T_J=25^\circ\text{C}$

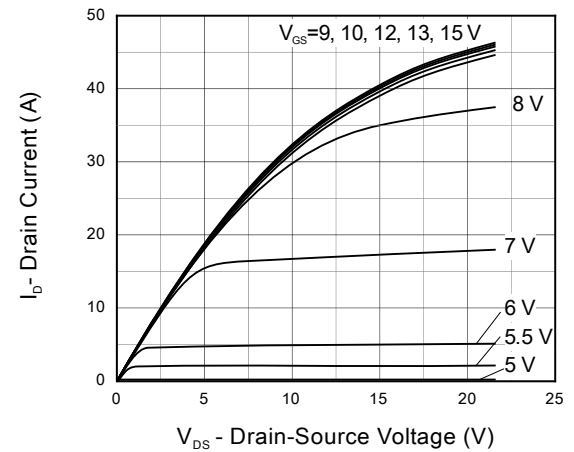


Fig 6. Output Characteristics
 $T_J=150^\circ\text{C}$

5. Electrical Characteristics (cont.)

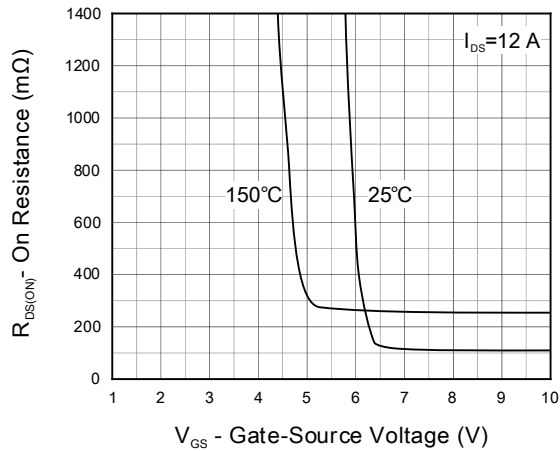


Fig 7. $R_{DS(ON)}$ vs. Gate Voltage

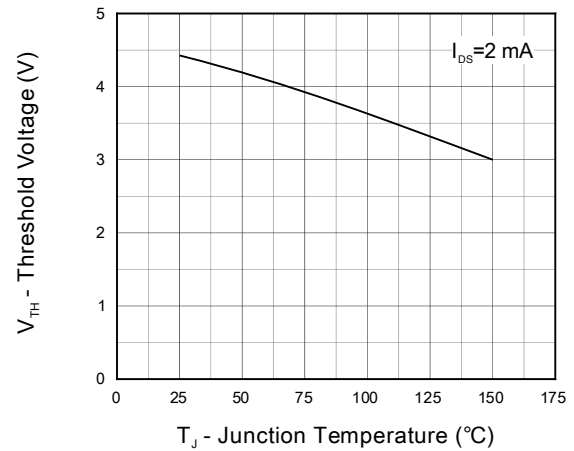


Fig 8. V_{TH} vs. Junction Temperature

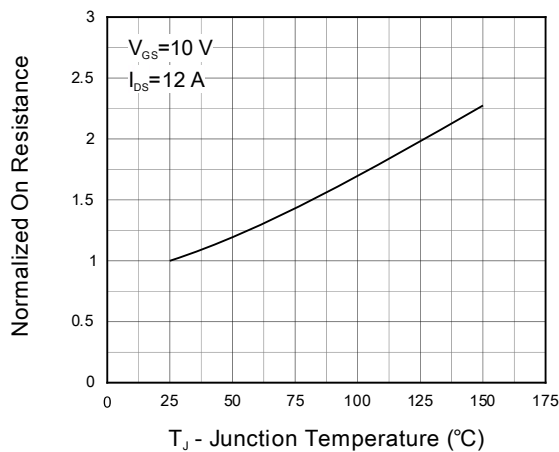


Fig 9. Normalized On Resistance

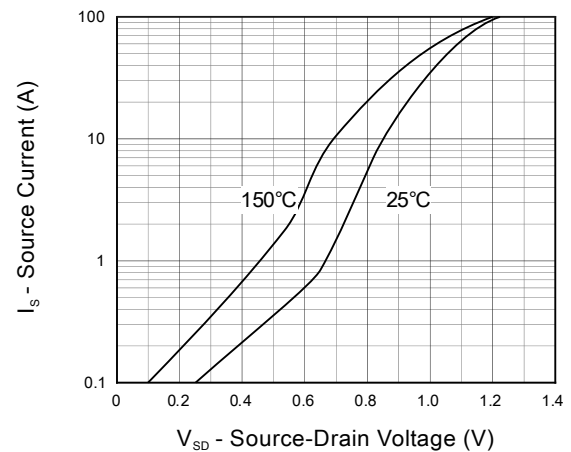


Fig 10. Diode Forward Current

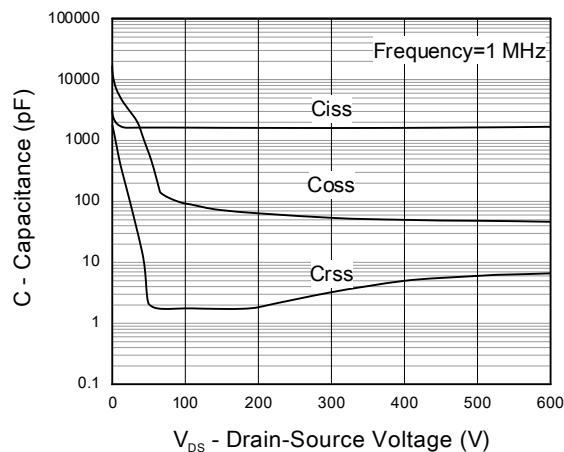


Fig 11. Capacitance

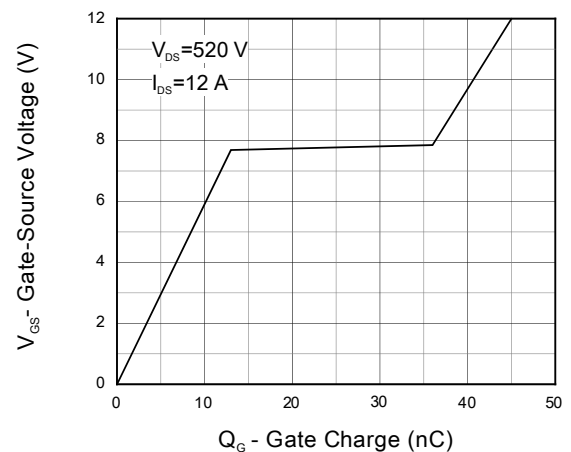
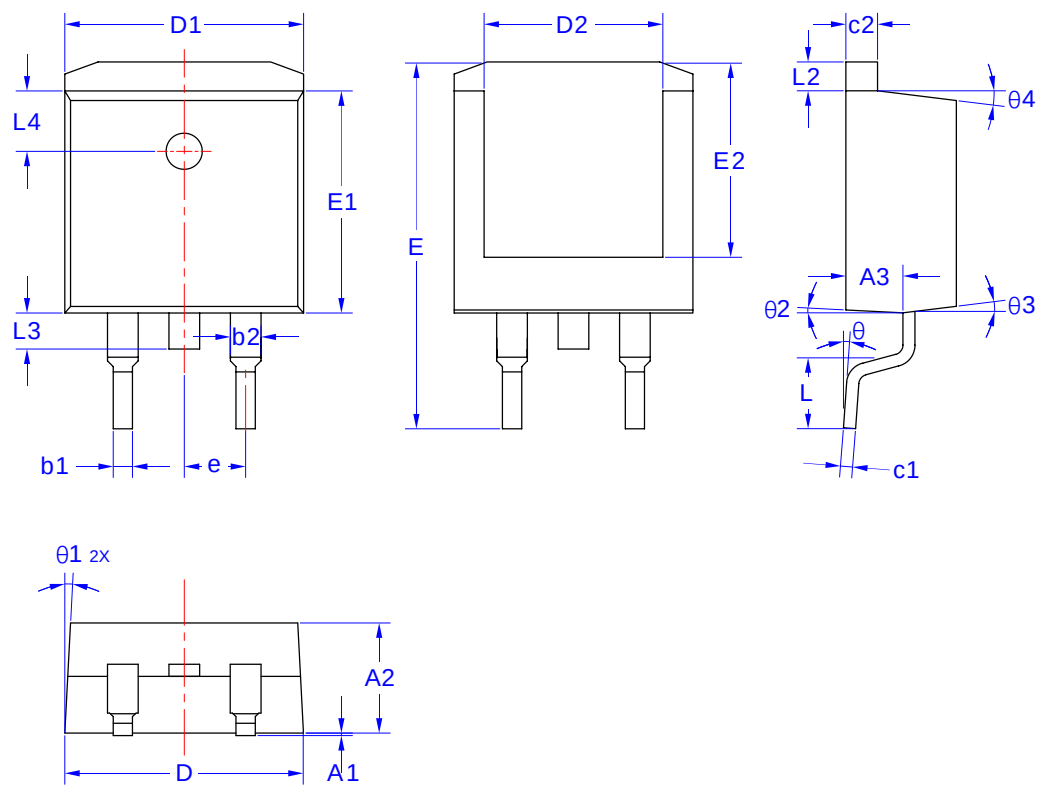


Fig 12. Gate Charge

5. Package Mechanical Data

TO-263 Package



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A1	0.020	-	0.200
A2	4.470	4.570	4.670
A3	2.300	2.350	2.400
b1	0.750	-	0.850
b2	1.220	-	1.320
c1	0.500	-	0.550
c2	1.300	-	1.350
D	9.780	9.880	9.980
D1		9.880 REF	
D2		7.400 REF	
E	14.900	15.100	15.300
E1	9.100	9.200	9.300

Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
E2		8.100 REF	
e		5.540 REF	
L	2.100	2.300	2.500
L2	1.025	-	1.375
L3	1.300	1.500	1.700
L4	2.400	2.500	2.600
θ		0~8°	
θ1		3°	
θ2		3°	
θ3		7°	
θ4		7°	